AMENDMENTS TO THE CLAIMS

1. (withdrawn): A method for forming a light emitting diode comprising following steps:
forming a first stack;
forming a second reaction layer over said first stack;
forming a second stack;
forming a first reaction layer over said second stack;
holding together said first reaction layer and said second reaction layer by means of a transparent adhesive layer.

2. (withdrawn): The method of claim 1 wherein the step of forming a first stack comprises following steps:
providing a first substrate;
forming a second contact layer on the first substrate;
forming a second cladding layer on the second contact layer;
forming an emitting layer on the second cladding layer;
forming a first cladding layer on the emitting layer;
forming a first contact layer on the first cladding layer; and
forming a transparent conductive layer on the first contact layer.

3. (withdrawn): The method of claim 2 further comprising following steps:
removing the first substrate;
etching the second contact layer, the second cladding layer, the emitting layer, first cladding layer, and the first contact layer; and
forming a first electrode on the second contact layer, and a second electrode on the transparent conductive layer.

4. (withdrawn): The method of claim 2 wherein the first substrate comprises at least one material selected from a group consisting of GaP, GaAs, and Ge.

5. (withdrawn): The method of claim 2 wherein the first contact layer and the

second contact layer each comprise at least one material selected from a group consisting of GaP, GaAs, GaAsP, InGaP, AlGaInP, and AlGaAs.

6. (withdrawn): The method of claim 2 wherein the first cladding layer, the emitting layer, and the second cladding layer each comprise AlGaInP.

7. (withdrawn): The method of claim 2 wherein the transparent conductive layer comprises at least one material selected from a group consisting of indium tin oxide, cadmium tin oxide, antimony tin oxide, zinc oxide, zinc tin oxide, BeAu, GeAu, and Ni/Au.

8. (withdrawn): The method of claim 1 wherein the first and second reaction layers each comprise at least one material selected from a group consisting of SiNx, Ti, and Cr.

9. (withdrawn): The method of claim 1 wherein the transparent adhesive layer comprises at least one material selected from a group consisting of PI, BCB, and PFCB.

10. (withdrawn): The method of claim 1 wherein forming a second stack comprises forming a second substrate.

11. (withdrawn): The method of claim 10 wherein the second substrate comprises at least one material selected from a group consisting of SiC, Al203, glass materials, quartz, GaP, GaAsP, and AlGaAs.

12. (withdrawn): The method of claim 1 wherein said first reaction layer and said second reaction layer are held together with the transparent adhesive layer by chemical bonds.

13. (withdrawn): The method of claim 12 wherein the chemical bonds are hydrogen bonds or ionic bonds.

14. (original): A light emitting diode comprising:
a first stack;
a second reaction layer formed on the first stack;
a second stack;
a first reaction layer formed on the second stack;
a transparent adhesive layer formed between the first and second reaction layers; and
a first electrode and a second electrode formed on the first stack.

15. (original): The light emitting diode of claim 14 wherein the first stack comprises:
a transparent conductive layer formed on the second reaction layer, the transparent conductive layer having a first surface area and a second surface area;
a first contact layer formed on the first surface area of the transparent conductive layer;
a first cladding layer formed on the first contact layer;
an emitting layer formed on the first cladding layer;
a second cladding layer formed on the emitting layer; and
a second contact layer formed on the second cladding layer;
wherein the first electrode is formed on the second contact layer, and the second electrode is formed on the second surface area of the transparent conductive layer.

16. (original): The light emitting diode of claim 15 wherein the first contact layer and the second contact layer each comprise at least one material selected from a group consisting of GaP, GaAs, GaAsP, InGaP, AlGaInP, and AlGaAs.

17. (original): The light emitting diode of claim 15 wherein the first cladding layer, the emitting layer, and the second cladding layer each comprise AlGaInP.

18. (original): The light emitting diode of claim 15 wherein the transparent conductive layer comprises at least one material selected from a group consisting of indium tin oxide, cadmium tin oxide, antimony tin oxide, zinc oxide, zinc tin oxide, BeAu, GeAu, and Ni/Au.

19. (original): The light emitting diode of claim 14 wherein the first and second reaction layers each comprise at least one material selected from a group consisting of SiNx, Ti, and Cr.

20. (original): The light emitting diode of claim 14 wherein the transparent adhesive layer comprises at least one material selected from a group consisting of PI, BCB, and PFCB.

21. (original): The light emitting diode of claim 14 wherein the second stack comprises a second substrate, the first reaction layer being formed on the second substrate.

22. (original): The light emitting diode of claim 21 wherein the second substrate comprises at least one material selected from a group consisting of SiC, Al203, glass materials, quartz, GaP, GaAsP, and AlGaAs.